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Kind regards,

Team Nexperia

## BAV756S; BAW56 series

# High-speed switching diodes Rev. 6 — 18 March 2015

**Product data sheet** 

#### 1. **Product profile**

### 1.1 General description

High-speed switching diodes, encapsulated in small Surface-Mounted Device (SMD) plastic packages.

Table 1. **Product overview** 

Type number	Package	_			Configuration
	NXP JEITA JEI		JEDEC	configuration	
BAV756S	SOT363	SC-88	-	very small	quadruple common anode/common cathode
BAW56	SOT23	-	TO-236AB	small	dual common anode
BAW56M	SOT883	SC-101	-	leadless ultra small	dual common anode
BAW56S	SOT363	SC-88	-	very small	quadruple common anode/common anode
BAW56T	SOT416	SC-75	-	ultra small	dual common anode
BAW56W	SOT323	SC-70	-	very small	dual common anode

#### 1.2 Features and benefits

- High switching speed: t<sub>rr</sub> ≤ 4 ns
- Low leakage current
- Small SMD plastic packages
- Low capacitance: C<sub>d</sub> ≤ 2 pF
- Reverse voltage: V<sub>R</sub> ≤ 90 V
- AEC-Q101 qualified

### 1.3 Applications

- High-speed switching
- General-purpose switching

### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Per diode							
I <sub>R</sub>	reverse current	V <sub>R</sub> = 80 V	-	-	0.5	μΑ	
$V_R$	reverse voltage		-	-	90	V	
t <sub>rr</sub>	reverse recovery time	<u>[1]</u>	-	-	4	ns	

<sup>[1]</sup> When switched from  $I_F$  = 10 mA to  $I_R$  = 10 mA;  $R_L$  = 100  $\Omega$ ; measured at  $I_R$  = 1 mA.



### 2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Symbol
BAV756S			
1	anode (diode 1)		
2	cathode (diode 2)	6 5 4	6 5 4
3	common anode (diode 2 and diode 3)	0	
4	cathode (diode 3)	1 2 3	
5	anode (diode 4)		1 2 3
6	common cathode (diode 1 and diode 4)		006aab103
<b>BAW56</b> ; <b>E</b>	BAW56T; BAW56W		
1	cathode (diode 1)		
2	cathode (diode 2)	3	3
3	common anode	1 2 006aaa144	1 2 006aab099
BAW56M			
1	cathode (diode 1)		
2	cathode (diode 2)	1 3	3
3	common anode	2 Transparent top view	1 2 006aab099
BAW56S			
1	cathode (diode 1)	П. П. П.	
2	cathode (diode 2)	6 5 4	6 5 4
3	common anode (diode 3 and diode 4)	0	
4	cathode (diode 3)	1 2 3	
5	cathode (diode 4)		1 2 3
6	common anode (diode 1 and diode 2)		006aab102

### 3. Ordering information

Table 4. Ordering information

Type number	Package					
	Name	e Description				
BAV756S	SC-88	plastic surface-mounted package; 6 leads	SOT363			
BAW56	-	plastic surface-mounted package; 3 leads	SOT23			
BAW56M	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 $\times$ 0.6 $\times$ 0.5 mm	SOT883			
BAW56S	SC-88	plastic surface-mounted package; 6 leads	SOT363			
BAW56T	SC-75	plastic surface-mounted package; 3 leads	SOT416			
BAW56W	SC-70	plastic surface-mounted package; 3 leads	SOT323			

### 4. Marking

Table 5. Marking codes

Type number	Marking code <sup>[1]</sup>
BAV756S	A7*
BAW56	A1*
BAW56M	S5
BAW56S	A1*
BAW56T	A1
BAW56W	A1*

<sup>[1] \* = -:</sup> made in Hong Kong

### 5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per diode					,
$V_{RRM}$	repetitive peak reverse voltage		-	90	V
$V_R$	reverse voltage		-	90	V
I <sub>F</sub>	forward current				
	BAV756S	T <sub>s</sub> = 60 °C	-	250	mA
	BAW56	T <sub>amb</sub> ≤ 25 °C	-	215	mA
	BAW56M	T <sub>amb</sub> ≤ 25 °C	-	150	mA
	BAW56S	T <sub>s</sub> = 60 °C	-	250	mA
	BAW56T	T <sub>s</sub> = 90 °C	-	150	mA
	BAW56W	T <sub>amb</sub> ≤ 25 °C	-	150	mA

BAV756S\_BAW56\_SER

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<sup>\* =</sup> p: made in Hong Kong

<sup>\* =</sup> t: made in Malaysia

<sup>\* =</sup> W: made in China

 Table 6.
 Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
I <sub>FRM</sub>	repetitive peak forward current		-	500	mA
I <sub>FSM</sub>	non-repetitive peak forward	square wave [1]			
	current	t <sub>p</sub> = 1 μs	-	4	Α
		t <sub>p</sub> = 1 ms	-	1	Α
		t <sub>p</sub> = 1 s	-	0.5	Α
P <sub>tot</sub>	total power dissipation	[2]			
	BAV756S	T <sub>s</sub> = 60 °C	-	350	mW
	BAW56	T <sub>amb</sub> ≤ 25 °C	-	250	mW
	BAW56M	$T_{amb} \le 25  ^{\circ}C$ [3]	-	250	mW
	BAW56S	T <sub>s</sub> = 60 °C	-	350	mW
	BAW56T	T <sub>s</sub> = 90 °C [4]	-	170	mW
	BAW56W	T <sub>amb</sub> ≤ 25 °C	-	200	mW
Per device	)				
l <sub>F</sub>	forward current				
	BAV756S	T <sub>s</sub> = 60 °C	-	100	mA
	BAW56	T <sub>amb</sub> ≤ 25 °C	-	125	mA
	BAW56M	T <sub>amb</sub> ≤ 25 °C	-	75	mA
	BAW56S	T <sub>s</sub> = 60 °C	-	100	mA
	BAW56T	T <sub>s</sub> = 90 °C	-	75	mA
	BAW56W	T <sub>amb</sub> ≤ 25 °C	-	130	mA
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup>  $T_j = 25$  °C prior to surge.

### 6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per diode							
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]				
	BAW56			-	-	500	K/W
	BAW56M		[2]	-	-	500	K/W
	BAW56W			-	-	625	K/W

<sup>[2]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>[3]</sup> Reflow soldering is the only recommended soldering method.

<sup>[4]</sup> Single diode loaded.

Table 7. Thermal characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point					
	BAV756S		-	-	255	K/W
	BAW56		-	-	360	K/W
	BAW56S		-	-	255	K/W
	BAW56T		-	-	350	K/W
	BAW56W		-	-	300	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Reflow soldering is the only recommended soldering method.

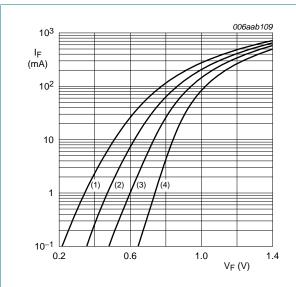
### 7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$  °C unless otherwise specified.

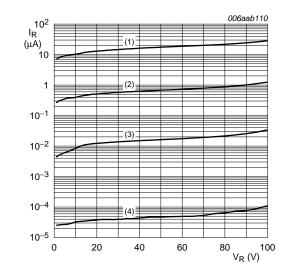
Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
Per diode								
$V_{F}$	forward voltage	[1]						
		I <sub>F</sub> = 1 mA	-	-	715	mV		
		I <sub>F</sub> = 10 mA	-	-	855	mV		
		I <sub>F</sub> = 50 mA	-	-	1	V		
		I <sub>F</sub> = 150 mA	-	-	1.25	V		
I <sub>R</sub>	reverse current	V <sub>R</sub> = 25 V	-	-	30	nA		
		V <sub>R</sub> = 80 V	-	-	0.5	μΑ		
		V <sub>R</sub> = 25 V; T <sub>j</sub> = 150 °C	-	-	30	μΑ		
		V <sub>R</sub> = 80 V; T <sub>j</sub> = 150 °C	-	-	150	μΑ		
C <sub>d</sub>	diode capacitance	V <sub>R</sub> = 0 V; f = 1 MHz	-	-	2	pF		
t <sub>rr</sub>	reverse recovery time	[2]	-	-	4	ns		
$V_{FR}$	forward recovery voltage	[3]	-	-	1.75	V		

- [1] Pulse test:  $t_p \le 300 \ \mu s; \ \delta \le 0.02.$
- [2] When switched from  $I_F$  = 10 mA to  $I_R$  = 10 mA;  $R_L$  = 100  $\Omega;$  measured at  $I_R$  = 1 mA.
- [3] When switched from  $I_F = 10$  mA;  $t_r = 20$  ns.



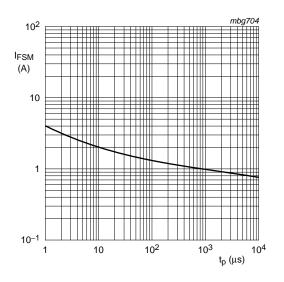
- (1)  $T_{amb} = 150 \, ^{\circ}C$
- (2)  $T_{amb} = 85 \, ^{\circ}C$
- (3)  $T_{amb} = 25 \, ^{\circ}C$
- (4)  $T_{amb} = -40 \, ^{\circ}C$

Fig 1. Forward current as a function of forward voltage; typical values



- (1)  $T_{amb} = 150 \, ^{\circ}C$
- (2)  $T_{amb} = 85 \, ^{\circ}C$
- (3)  $T_{amb} = 25 \, ^{\circ}C$
- (4)  $T_{amb} = -40 \, ^{\circ}C$

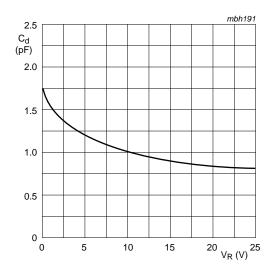
Fig 3. Reverse current as a function of reverse voltage; typical values



Based on square wave currents.

 $T_i = 25$  °C; prior to surge

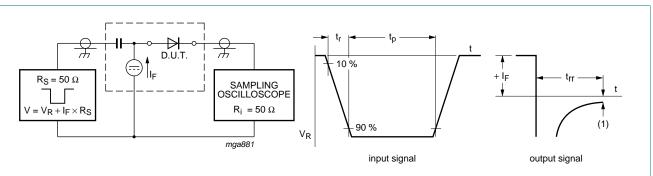
Fig 2. Non-repetitive peak forward current as a function of pulse duration; maximum values



 $f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^{\circ}\text{C}$ 

Fig 4. Diode capacitance as a function of reverse voltage; typical values

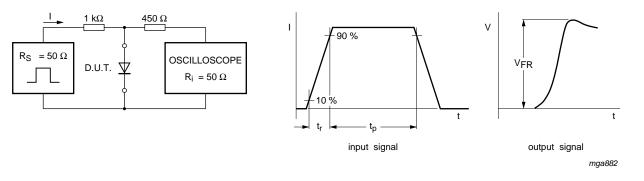
### 8. Test information



(1)  $I_R = 1 \text{ mA}$ 

Input signal: reverse pulse rise time  $t_r$  = 0.6 ns; reverse voltage pulse duration  $t_p$  = 100 ns; duty cycle  $\delta$  = 0.05 Oscilloscope: rise time  $t_r$  = 0.35 ns

Fig 5. Reverse recovery time test circuit and waveforms



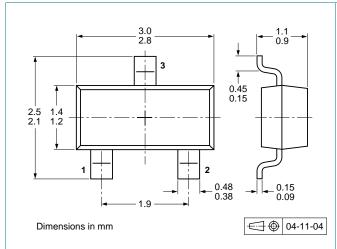
Input signal: forward pulse rise time  $t_r$  = 20 ns; forward current pulse duration  $t_p \ge 100$  ns; duty cycle  $\delta \le 0.005$ 

Fig 6. Forward recovery voltage test circuit and waveforms

### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### 9. Package outline



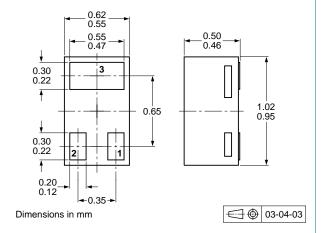
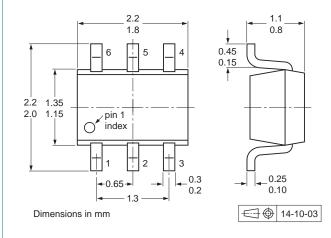


Fig 7. Package outline BAW56 (SOT23/TO-236AB)

Fig 8. Package outline BAW56M (SOT883/SC-101)



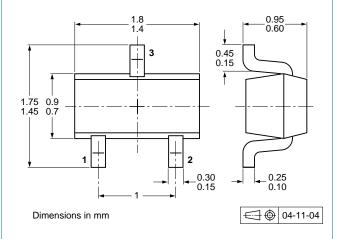


Fig 9. Package outline BAV756S and BAW56S (SOT363/SC-88)

Fig 10. Package outline BAW56T (SOT416/SC-75)

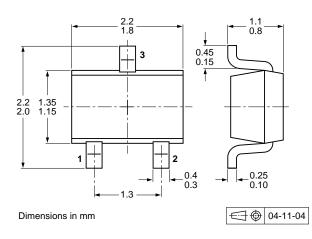


Fig 11. Package outline BAW56W (SOT323/SC-70)

BAV756S\_BAW56\_SER

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### 10. Packing information

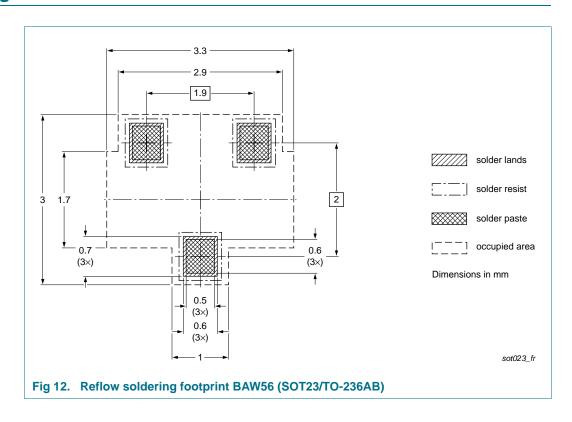
Table 9. Packing methods

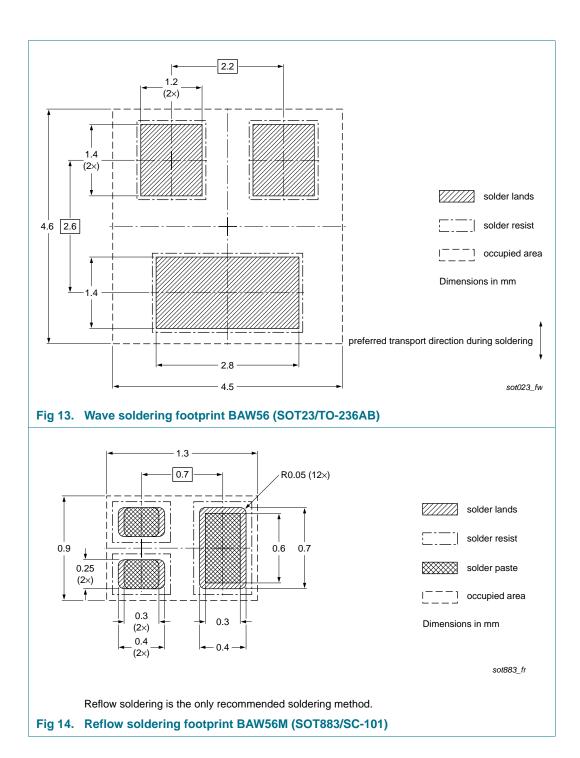
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

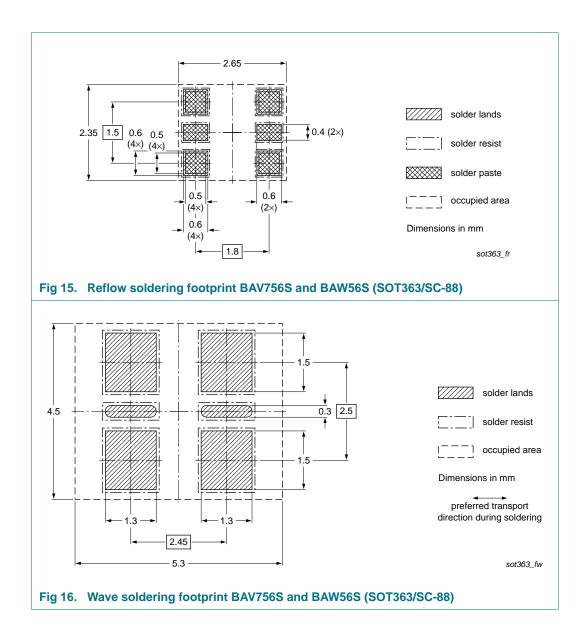
Type number	Package	e Description		uantity
			3000	10000
BAV756S	SOT363	4 mm pitch, 8 mm tape and reel; T1	-115	-135
		4 mm pitch, 8 mm tape and reel; T2	-125	-165
BAW56	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235
BAW56M	SOT883	2 mm pitch, 8 mm tape and reel	-	-315
BAW56S	SOT363	4 mm pitch, 8 mm tape and reel; T1 [2]	-115	-135
		4 mm pitch, 8 mm tape and reel; T2	-125	-165
BAW56T	SOT416	4 mm pitch, 8 mm tape and reel	-115	-135
BAW56W	SOT323	4 mm pitch, 8 mm tape and reel	-115	-135

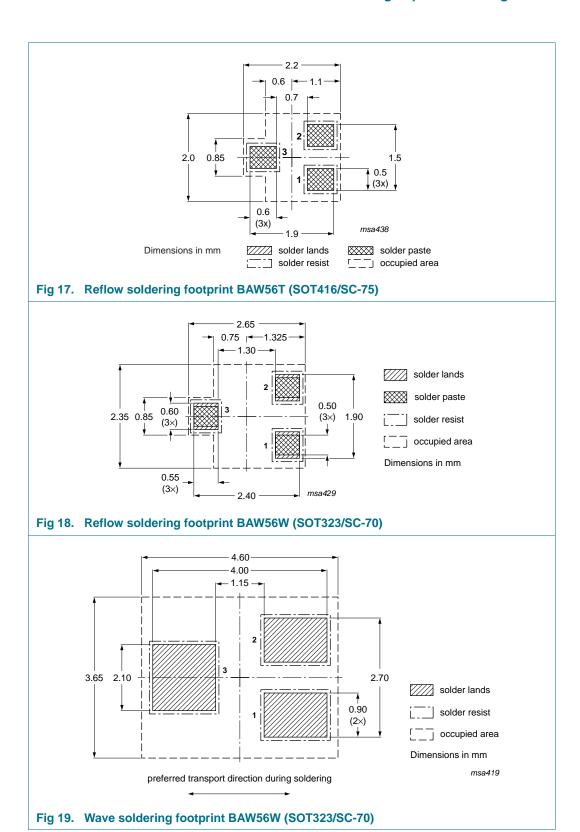
- [1] For further information and the availability of packing methods, see Section 14.
- [2] T1: normal taping
- [3] T2: reverse taping

### 11. Soldering









### 12. Revision history

#### Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BAV756S_BAW56_SER v.6	20150318	Product data sheet	-	BAV756S_BAW56_SER_ 5	
Modifications:	<ul> <li>The format of this data sheet has been redesigned to comply with the new ide guidelines of NXP Semiconductors.</li> </ul>				
	<ul> <li>Legal texts ha</li> </ul>	ave been adapted to the new	company name whe	ere appropriate.	
BAV756S_BAW56_SER_5	20071126	Product data sheet	-	BAV756S_2 BAW56_4 BAW56S_2 BAW56T_2 BAW56W_4	
BAV756S_2	19971021	Product specification	-	BAV756S_1	
BAW56_4	20030325	Product specification	-	BAW56_3	
BAW56S_2	19971021	Product specification	-	BAW56S_1	
BAW56T_2	19971219	Product specification	-	-	
BAW56W_4	19990511	Product specification	-	BAW56W_3	

### 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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BAV756S\_BAW56\_SER

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### BAV756S; BAW56 series

#### **High-speed switching diodes**

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## BAV756S; BAW56 series

### **NXP Semiconductors**

**High-speed switching diodes** 

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